

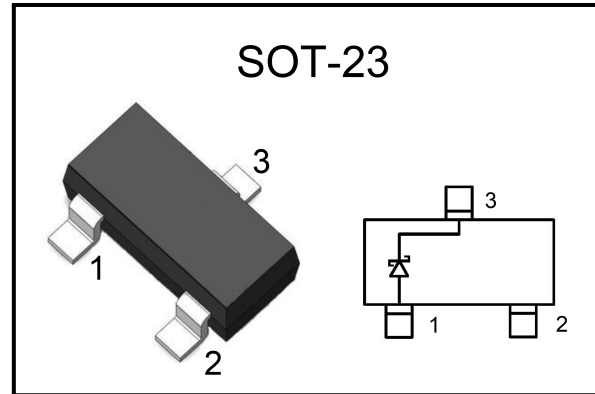
BAS116

Schottky Barrier Diode

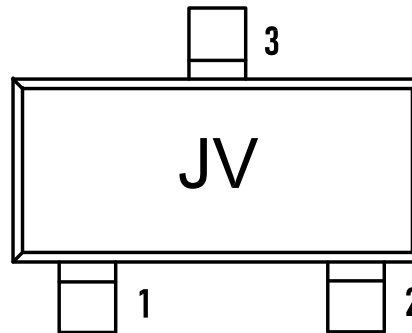
Features

- Low forward voltage drop
- Guard Ring Construction for Transient Protection.
- Negligible Reverse Recovery Time.
- Low Reverse Capacitance.
- Low Leakage Current Applications.
- Medium speed switching times .

Package



Marking



Ordering information

Order code	Package	Marking	Base qty	Delivery mode
BAS116	SOT-23	JV	3K	Tape and reel

Maximum Ratings (@T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{RRM}	Peak Repetitive Peak Reverse Voltage	75	V
V _{RWM}	Working Peak Reverse Voltage		
V _R	DC Blocking Voltage		
I _{FM}	Forward Continuous Current	200	mA
I _{FSM}	Non-repetitive Peak Forward Surge Current @8.3mS	2.0	A
P _D	Power Dissipation	200	mW
R _{θJA}	Typical thermal resistance	667	°C/W
T _j	Operating junction Temperature Range	-55 to +150	°C
T _{STG}	Storage temperature Range	-55 to +150	°C





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Schottky Barrier Diode

Electrical Characteristics(@T_A=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V _(BR)	Reverse breakdown voltage	I _R =100μA	75	–	–	V
I _R	Reverse voltage leakage current	V _R =75V	–	–	5	nA
V _F	Forward voltage	I _F =1mA	–	–	0.9	V
		I _F =10mA	–	–	1	
		I _F =50mA	–	–	1.1	
		I _F =150mA	–	–	1.25	
C _j	Type junction capacitance	V _R =0V, f=1MHZ	–	2	–	pF
T _{rr}	Reverse recovery time	I _F =I _R = 10mA, I _{rr} =0.1X I _R ,R _L =100Ω	–	–	3	nS



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Typical Performance Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Figure 1: Forward Characteristics

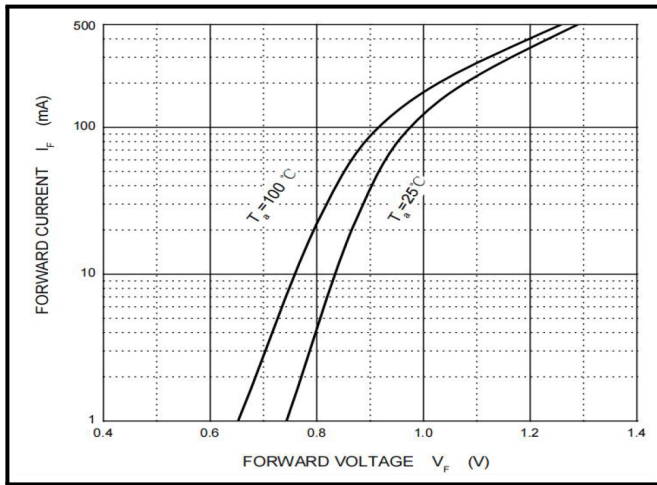


Figure 2: Reverse Characteristics

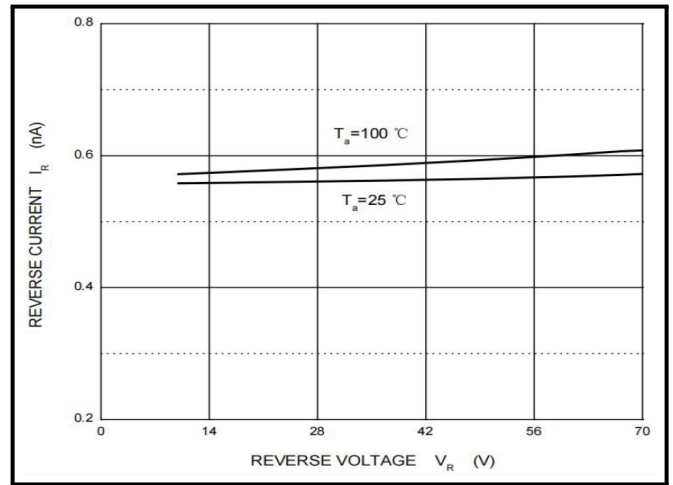


Figure 3: Capacitance Characteristics

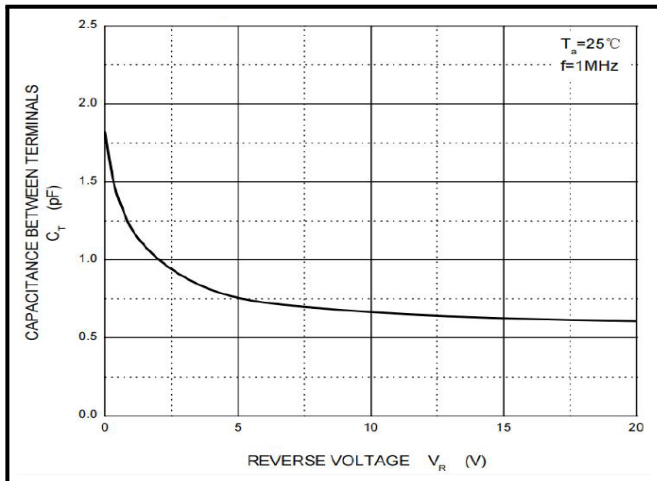
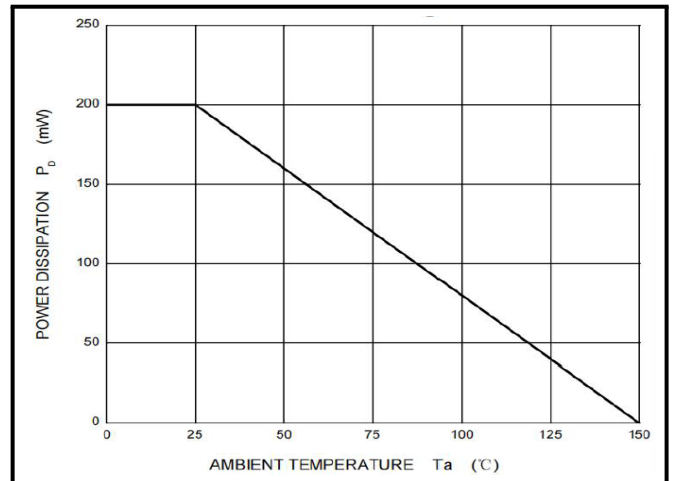


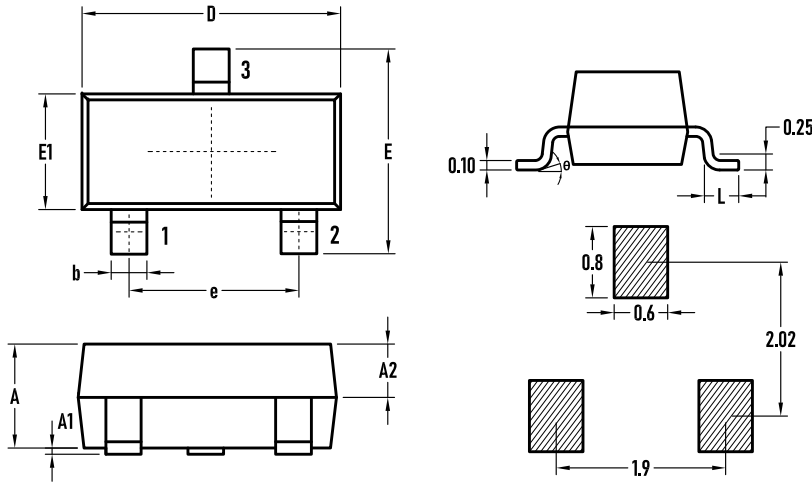
Figure 4: Power Derating Curve



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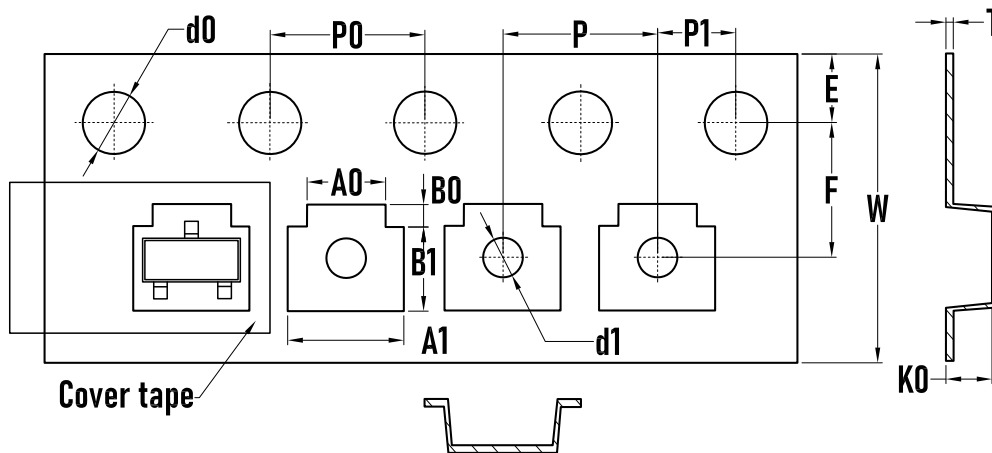
Schottky Barrier Diode

Outline Drawing - SOT-23



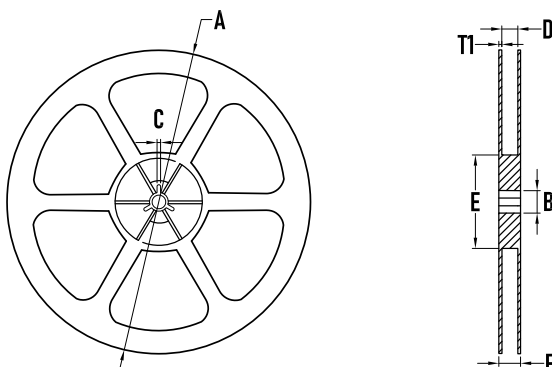
SYMBOL	MILLIMETER		
	MIN.	Typ.	MAX.
A	0.95	1.00	—
A1	0.02	0.06	0.10
A2	—	0.60	—
D	2.85	2.90	2.95
b	0.37	0.40	0.43
E	2.35	2.40	2.45
E1	1.25	1.30	1.35
e	1.85	1.90	1.95
L	0.35	0.40	0.48
θ	0	—	6°

Packaging Tape - SOT-23



SYMBOL	MILLIMETER
A0	2.10±0.10
A1	3.10±0.10
B0	0.65±0.10
B1	2.75±0.10
d0	1.55±0.10
d1	1.00±0.05
E	1.75±0.10
F	3.50±0.10
K0	1.10±0.10
P	4.00±0.10
P0	4.00±0.10
P1	2.00±0.10
W	8.00±0.30
T	0.20 ±0.05

Packaging Reel



SYMBOL	MILLIMETER
A	177.8±0.2
B	3.1
C	13.50
D	9.6±0.3
E	75±0.2
F	12.3±0.3
T1	1.0±0.2
Quantity	3000PCS

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